

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Overall Thickness	681.00 +/- 6.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%
	10.0	Edge Exclusion	7mm	
	HandleSilicon	11.0	Handle Growth Method	CZ
12.0		Handle Orientation	{100} +/- 1 degree	Wafer Vendor
13.0		Handle Thickness	600.00 +/- 5.00 µm	ADE, 100%
14.0		Handle Doping Type	N	Wafer Vendor
15.0		Handle Dopant	Phosphorous	Wafer Vendor
16.0		Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
17.0		Backside Finish	Lapped and Etched	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Device Wafer	
DeviceSilicon	21.0	Device Growth Method	Low Oi CZ	Wafer Vendor
	22.0	Oxygen Concentration	<13.40ppma	New ASTM
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	76.00 +/- 2.00 µm	FTIR, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	< 5mm	Typical by Process, no edge grind.
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorous	Wafer Vendor
	28.0	Device Resistivity	1 - 3 Ohm-cm	Wafer Vendor
	32.0	Voids	0	Bright Light, 100% (note2)
	33.0	Scratches	<25mm total length	Bright Light, 100% (note2)
	34.0	Haze	none	Bright Light, 100% (note2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information